

**Amendments to the Claims:**

**Listing of Claims:**

5      Claims 1-241 (canceled)

242. (currently amended) A method for fabricating a chip package comprising:

                 joining a die and a substrate, wherein said die ~~has having~~ a top surface at a  
horizontal level, wherein said die and said substrate are under said horizontal  
10      level;

                 after said joining said die and said substrate, forming a patterned circuit  
layer over said horizontal level, wherein said patterned circuit layer extends  
~~extending~~ across an edge of said die;

                 after said joining said die and said substrate, forming a passive device over  
15      said substrate and over said horizontal level, wherein said passive device  
comprises a part is entirely not directly over ~~said any~~ die; and

after said forming said patterned circuit layer and said forming said  
passive device, separating said substrate into multiple portions.

20      243. (currently amended) A method for fabricating a chip package comprising:

providing a first die having a first top surface at a horizontal level;  
providing a second die having a second top surface at said horizontal level;  
forming a polymer between said first and second dies;

~~joining a die and a substrate, said die having a top surface at horizontal~~  
25      ~~level, wherein said die and said substrate are under said horizontal level;~~

~~after said joining said die and said substrate, after said forming said~~  
polymer, forming a passive device over said horizontal level, wherein said passive  
device ~~has having~~ a first connection point connected to said first die; and

                 after said forming said passive device, forming a metal bump over said  
30      horizontal level, wherein said metal bump is connected to a second connection  
point of said passive device, ~~and~~

~~separating said substrate into multiple portions.~~

244. (currently amended) A method for fabricating a chip package comprising:

providing a first die having a first top surface at a horizontal level;

5 providing a second die having a second top surface at said horizontal level;

forming a polymer between said first and second dies;

after said forming said polymer, forming a passive device over said  
horizontal level, wherein said passive device has a ~~portion-part~~ not directly over  
any die; said first and second dies;

10 after said forming said passive device over said horizontal level, forming  
an insulating layer on said passive device; and

after said forming said polymer, forming a patterned circuit layer over said  
horizontal level, wherein said patterned circuit layer extends across an edge of  
said first or second die.

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245. (previously presented) The method of claim 242, wherein said substrate  
comprises a metal substrate.

246. (currently amended) The method of claim 242 further comprising joining a  
20 film and said substrate, wherein an opening in said film exposes ~~exposing~~ said  
substrate, followed by said joining said die and said substrate exposed by said  
opening.

247. (currently amended) The method of claim 246, wherein forming said opening  
25 in said film ~~comprising~~ comprises a punching process.

248. (previously presented) The method of claim 246, wherein said film  
comprises a metal layer.

30 Claim 249 (canceled)

250. (previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises an electroplating process.

5 251. (previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises a sputtering process.

252. (previously presented) The method of claim 242, wherein said forming said passive device comprises an electroplating process.

10 253. (withdrawn) The method of claim 242, wherein said forming said passive device comprises a sputtering process.

15 254. (previously presented) The method of claim 242, after said joining said die and said substrate, further comprising forming a solder bump over said horizontal level, followed by said separating said substrate.

20 255. (withdrawn) The method of claim 242, after said joining said die and said substrate, further comprising forming a gold bump over said horizontal level, followed by said separating said substrate.

256. (currently amended) The method of claim 242, wherein said passive device comprises an inductor. ~~forming said patterned circuit layer and said forming said passive device are followed by said separating said substrate.~~

25 257. (currently amended) The method of claim 243 further comprising joining said first die and a substrate and joining said second die and said substrate, followed by said forming said polymer. ~~wherein said substrate comprises a metal substrate.~~

30 258. (currently amended) The method of claim 257, 243 ~~wherein said substrate comprises a metal substrate.~~ further comprising joining a film and said substrate,

~~an opening in said film exposing said substrate, followed by said joining said die  
and said substrate exposed by said opening.~~

259. (currently amended) The method of claim ~~257, 258~~, after said forming said  
5 metal bump, further comprising separating said substrate into multiple portions.  
~~wherein forming said opening in said film comprising a punching process.~~

260. (currently amended) The method of claim ~~243, 258~~, wherein said polymer  
comprises an epoxy. film comprises a metal layer.

10 261. (currently amended) The method of claim 243, after said forming said  
polymer, joining said die and said substrate, further comprising forming a  
patterned circuit layer over said horizontal level, wherein said patterned circuit  
layer extends ~~extending~~ across an edge of said first die, followed by said forming  
15 said metal bump. separating said substrate.

262. (previously presented) The method of claim 261, wherein said forming said  
patterned circuit layer comprises an electroplating process.

20 263. (previously presented) The method of claim 261, wherein said forming said  
patterned circuit layer comprises a sputtering process.

264. (previously presented) The method of claim 243, wherein said forming said  
passive device comprises an electroplating process.

25 265. (withdrawn) The method of claim 243, wherein said forming said passive  
device comprises a sputtering process.

266. (previously presented) The method of claim 243, wherein said forming said  
30 metal bump comprises forming a solder bump over said horizontal level, wherein  
said solder bump is connected to said second connection point.

267. (withdrawn) The method of claim 243, wherein said forming said metal bump comprises forming a gold bump over said horizontal level, wherein said gold bump is connected to said second connection point.

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268. (currently amended) The method of claim 243, wherein said passive device comprises an inductor. ~~forming said metal bump is followed by said separating said substrate.~~

10 269. (previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises an electroplating process.

270. (previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises a sputtering process.

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271. (previously presented) The method of claim 244, wherein said forming said passive device comprises an electroplating process.

20 272. (withdrawn) The method of claim 244, wherein said forming said passive device comprises a sputtering process.

273. (previously presented) The method of claim 244, after said forming said insulating layer and said forming said patterned circuit layer, further comprising forming a solder bump over said horizontal level.

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274. (withdrawn) The method of claim 244, after said forming said insulating layer and said forming said patterned circuit layer, further comprising forming a gold bump over said horizontal level.

30 275. (new) The method of claim 244, wherein said passive device comprises an inductor.

276. (new) The method of claim 244, wherein said passive device comprises a capacitor.

5 277. (new) The method of claim 244, wherein said passive device comprises a resistor.

278. (new) The method of claim 244, wherein said passive device comprises a filter.

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279. (new) The method of claim 244, wherein said polymer comprises an epoxy.

280. (new) The method of claim 244 further comprising joining said first die and a substrate and joining said second die and said substrate, followed by said  
15 forming said polymer.

281. (new) The method of claim 280, wherein said substrate comprises a metal substrate.

20 282. (new) The method of claim 280, after said forming said insulating layer and said forming said patterned circuit layer, further comprising separating said substrate into multiple portions.

283. (new) The method of claim 242, wherein said passive device comprises a  
25 capacitor.

284. (new) The method of claim 242, wherein said passive device comprises a resistor.

30 285. (new) The method of claim 242, wherein said passive device comprises a filter.

286. (new) The method of claim 243, wherein said passive device comprises a capacitor.

- 5    287. (new) The method of claim 243, wherein said passive device comprises a resistor.

288. (new) The method of claim 243, wherein said passive device comprises a filter.